

ABSTRACT OF THE DISCLOSURE

A high-quality light emitting device is provided which has a long-lasting light emitting element free from the problems of conventional ones because of a structure that
5 allows less degradation, and a method of manufacturing the light emitting device is provided. After a bank is formed, an exposed anode surface is wiped using a PVA (polyvinyl alcohol) -based porous substance or the like to level the surface and remove dusts from the surface. An insulating film is formed between an interlayer insulating film on a TFT and the anode. Alternatively, plasma treatment is performed on the surface of
10 the interlayer insulating film on the TFT for surface modification.